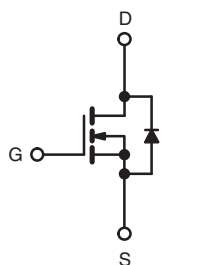
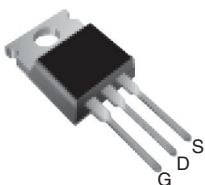


Power MOSFET

PRODUCT SUMMARY

V_{DS} (V)	50	
$R_{DS(on)}$ (Ω)	$V_{GS} = 10\text{ V}$	0.10
Q_g (Max.) (nC)	17	
Q_{gs} (nC)	9.0	
Q_{gd} (nC)	3.0	
Configuration	Single	

TO-220AB


N-Channel MOSFET

FEATURES

- Extremely Low $R_{DS(on)}$
- Compact Plastic Package
- Fast Switching
- Low Drive Current
- Ease of Paralleling
- Excellent Temperature Stability
- Parts Per Million Quality
- Compliant to RoHS Directive 2002/95/EC



Available

RoHS*
COMPLIANT

DESCRIPTION

The technology has expanded its product base to serve the low voltage, very low $R_{DS(on)}$ MOSFET transistor requirements. Vishay's highly efficient geometry and unique processing have been combined to create the lowest on resistance per device performance. In addition to this feature all have documented reliability and parts per million quality!

The transistor also offer all of the well established advantages of MOSFETs such as voltage control, very fast switching, ease of paralleling, and temperature stability of the electrical parameters.

They are well suited for applications such as switching power supplies, motor controls, inverters, choppers, audio amplifiers, high energy pulse circuits, and in systems that are operated from low voltage batteries, such as automotive, portable equipment, etc.

ORDERING INFORMATION

Package	TO-220AB
Lead (Pb)-free	IRFZ20PbF SiHFZ20-E3
SnPb	IRFZ20 SiHFZ20

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage ^a	V_{DS}	50	V
Gate-Source Voltage ^a	V_{GS}	± 20	
Continuous Drain Current	V_{GS} at 10 V	$T_C = 25\text{ }^\circ\text{C}$	A
		$T_C = 100\text{ }^\circ\text{C}$	
Pulsed Drain Current ^b	I_{DM}	60	
Single Pulse Avalanche Energy ^c	E_{AS}	5	mJ
Linear Derating Factor (see fig. 16)		0.32	W/ $^\circ\text{C}$
Maximum Power Dissipation (see fig. 16)	P_D	40	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 150	$^\circ\text{C}$
Soldering Recommendations (Peak Temperature)	for 10 s	300 (0.063" (1.6 mm) from case	

Notes

a. $T_J = 25\text{ }^\circ\text{C}$ to $150\text{ }^\circ\text{C}$

b. Repetitive rating: Pulse width limited by max. junction temperature. See transient temperature impedance curve (see fig. 11).

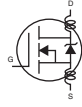
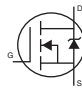
c. Starting $T_J = 25\text{ }^\circ\text{C}$, $L = 0.07\text{ mH}$, $R_g = 25\text{ }\Omega$, $I_{AS} = 12\text{ A}$

* Pb containing terminations are not RoHS compliant, exemptions may apply

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Typical Socket Mount, Junction-to-Ambient	R_{thJA}	-	80	°C/W
Case-to-Sink, Mounting Surface Flat, Smooth, and Greased	R_{thCS}	1.0	-	
Junction-to-Case	R_{thJC}	-	3.12	

ELECTRICAL CHARACTERISTICS ($T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA		50	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		2.0	-	4.0	V
Gate-Source Leakage	I _{GSS}	V _{GS} = ± 20 V		-	-	± 500	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} > Max. Rating, V _{GS} = 0 V		-	-	250	μA
		V _{DS} = Max. Rating x 0.8, V _{GS} = 0 V, T _C = 125 °C		-	-	1000	
On-State Drain Current	I _{D(on)}	V _{GS} = 10 V	V _{DS} > I _{D(on)} x R _{DS(on)} max.	-	-	15	A
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = 10 V	I _D = 10 A	-	0.080	0.10	Ω
Forward Transconductance ^b	g _{fs}	V _{DS} > I _{D(on)} x R _{DS(on)} max., I _D = 9.0 A		5.0	6.0	-	S
Dynamic							
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1.0 MHz, see fig. 11		-	560	860	pF
Output Capacitance	C _{oss}			-	250	350	
Reverse Transfer Capacitance	C _{rss}			-	60	100	
Total Gate Charge	Q _g	V _{GS} = 10 V	I _D = 20 A, V _{DS} = 0.8 max. rating, see fig. 18 for test circuit (Gate charge is essentially independent of operating temperature)	-	12	17	nC
Gate-Source Charge	Q _{gs}			-	9.0	-	
Gate-Drain Charge	Q _{gd}			-	3.0	-	
Turn-On Delay Time	t _{d(on)}	V _{DD} = 25 V, I _D = 9.0 A, Z ₀ = 50 Ω, see fig. 5 ^b		-	15	30	ns
Rise Time	t _r			-	45	90	
Turn-Off Delay Time	t _{d(off)}			-	20	40	
Fall Time	t _f			-	15	30	
Internal Drain Inductance	L _D	Modified MOSFET symbol showing the internal device inductances 		-	3.5	-	nH
Internal Source Inductance	L _S			-	4.5	-	
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I _S	MOSFET symbol showing the integral reverse p - n junction rectifier 		-	-	15	A
Pulsed Diode Forward Current ^a	I _{SM}			-	-	60	
Body Diode Voltage ^b	V _{SD}	T _C = 25 °C, I _S = 15 A, V _{GS} = 0 V		-	-	1.5	V
Body Diode Reverse Recovery Time	t _{rr}	T _J = 150 °C, I _F = 15 A, dI _F /dt = 100 A/μs		-	100	-	ns
Body Diode Reverse Recovery Charge	Q _{rr}			-	0.4	-	μC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L _S and L _D)					

Notes

- a. Repetitive rating: Pulse width limited by max. junction temperature. See transient temperature impedance curve (see fig. 5).
b. Pulse test: Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

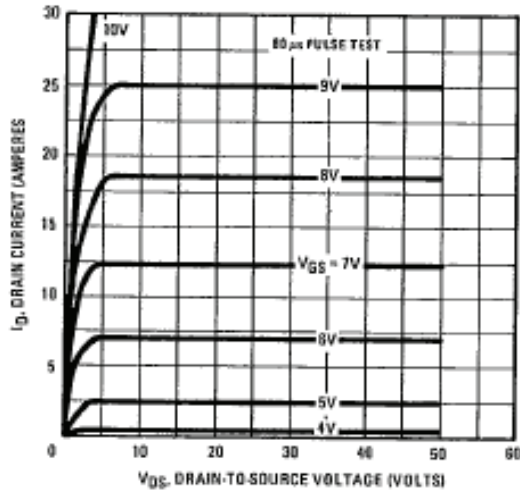


Fig. 1 - Typical Output Characteristics

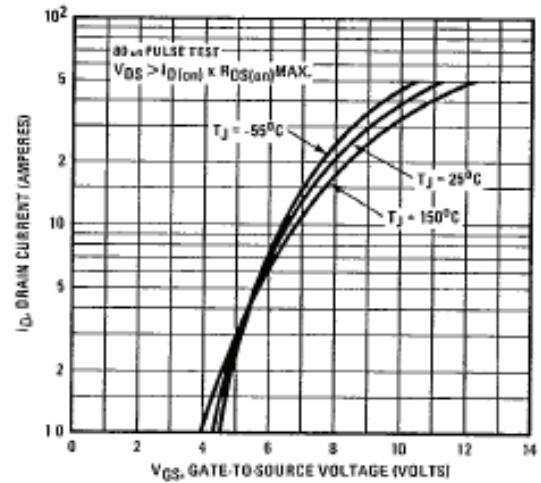


Fig. 3 - Typical Transfer Characteristics

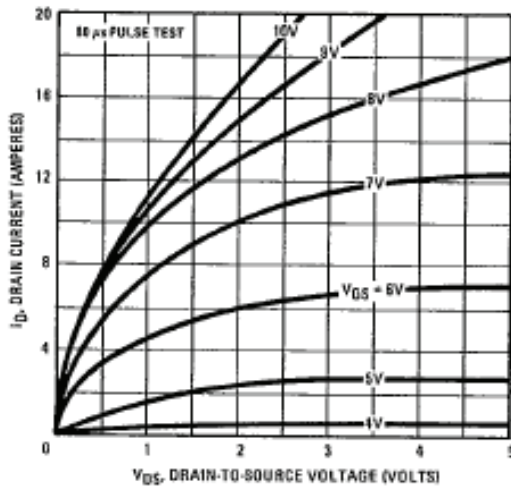


Fig. 2 - Typical Saturation Characteristics

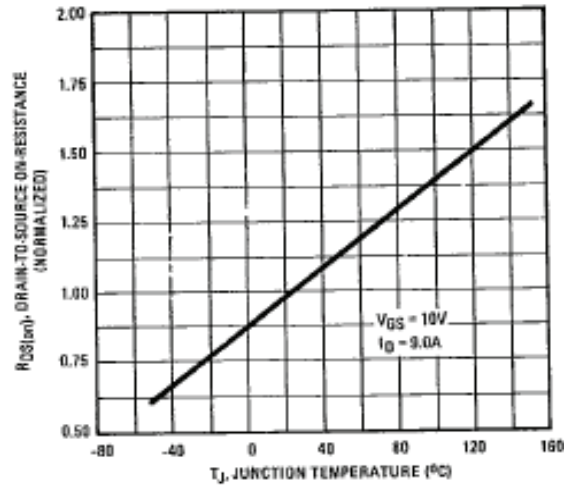


Fig. 4 - Normalized On-Resistance vs. Temperature

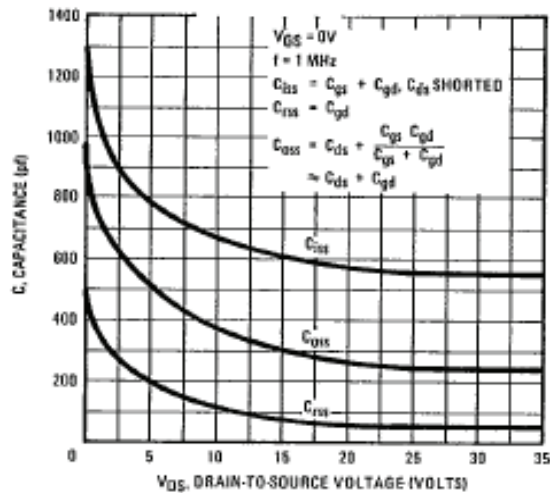


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

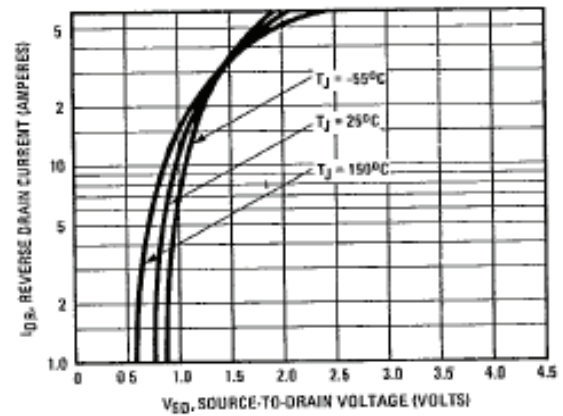


Fig. 7 - Typical Source-Drain Diode Forward Voltage

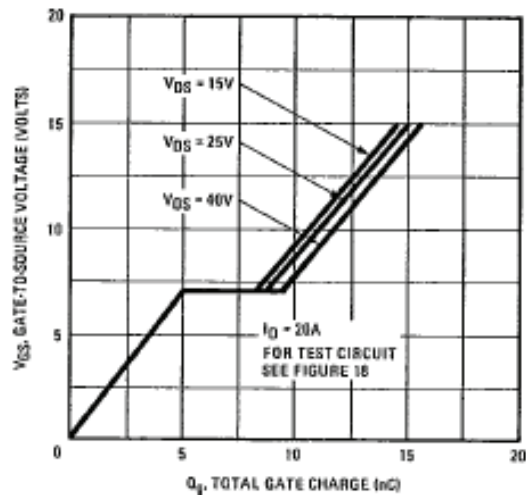


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

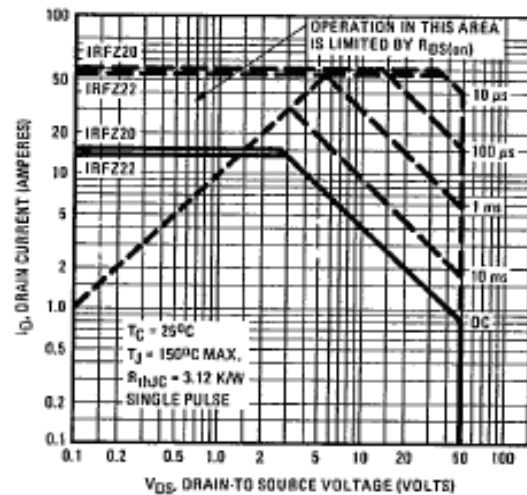


Fig. 8 - Maximum Safe Operating Area

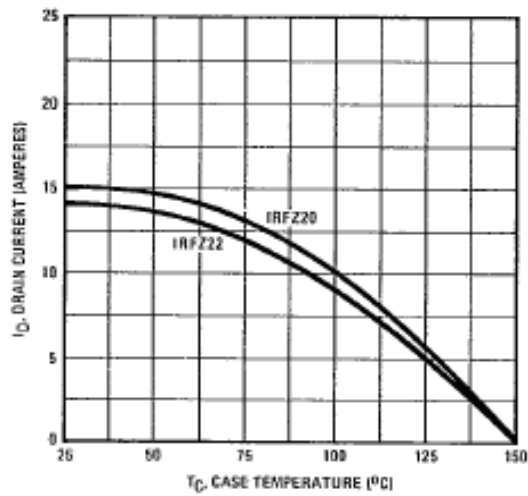


Fig. 9 - Maximum Drain Current vs. Case Temperature

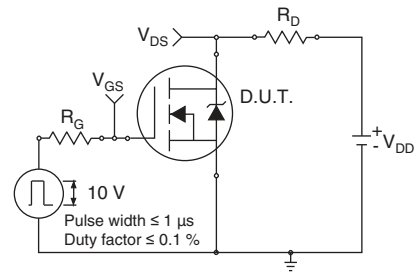


Fig. 10a - Switching Time Test Circuit

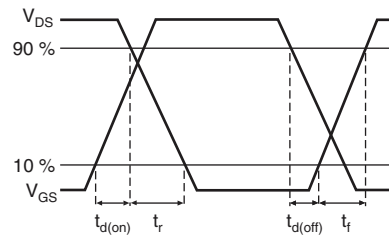


Fig. 10b - Switching Time Waveforms

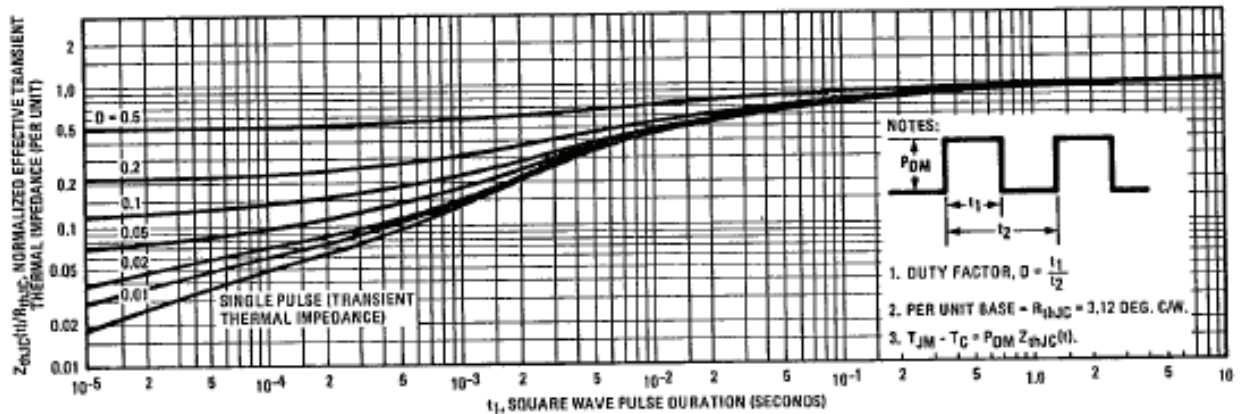


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case vs. Pulse Duration

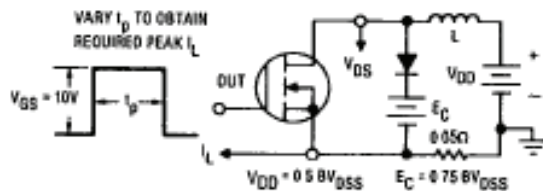


Fig. 12a - Clamped Inductive Test Circuit

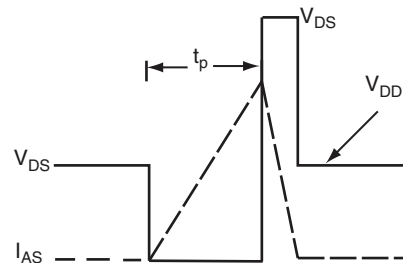


Fig. 12b - Unclamped Inductive Waveforms

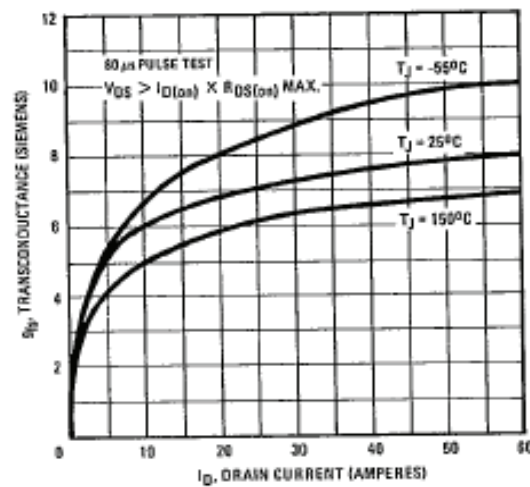


Fig. 13 - Typical Transconductance vs. Drain Current

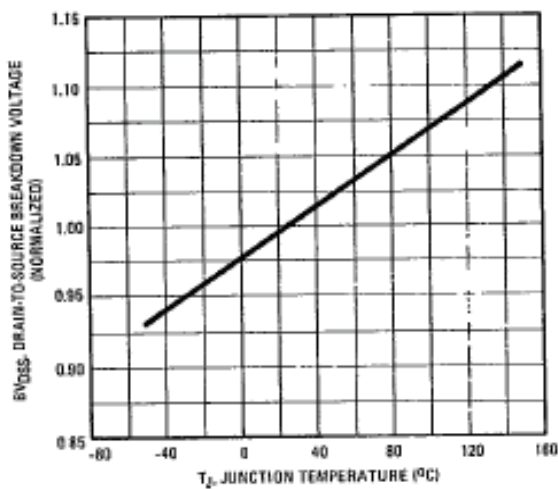


Fig. 14 - Breakdown Voltage vs. Temperature

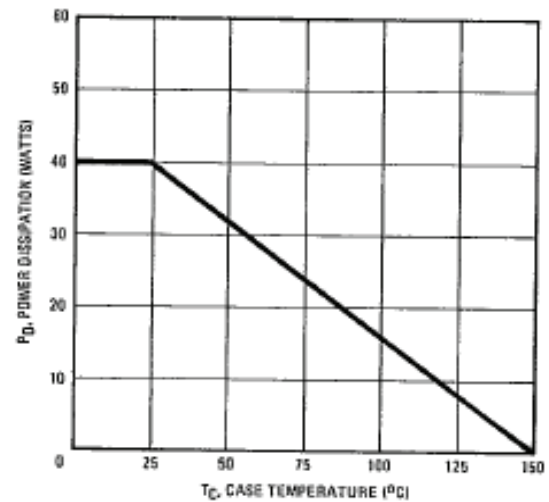


Fig. 16 - Power vs. Temperature Derating Curve

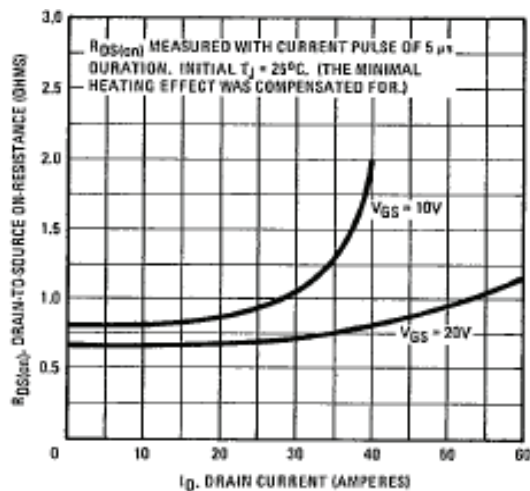


Fig. 15 - Typical On-Resistance vs. Drain Current

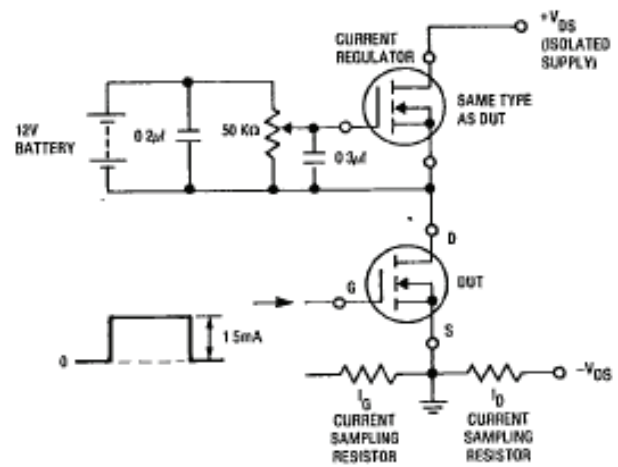
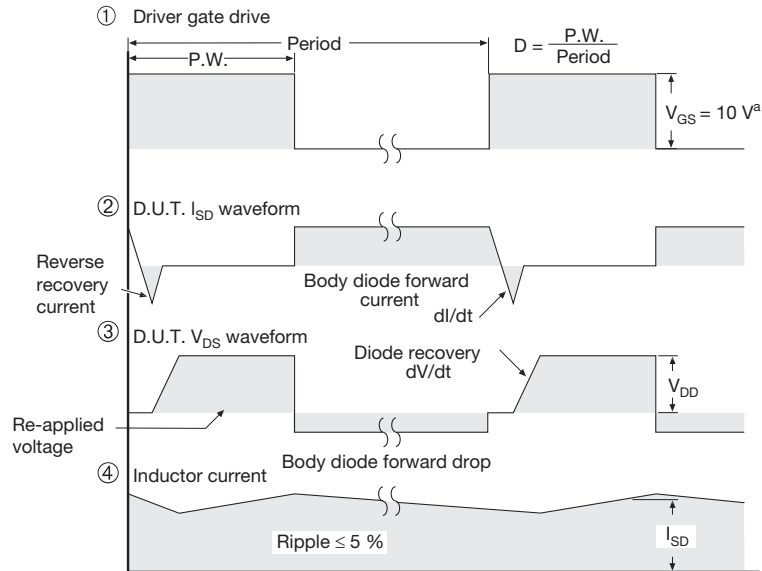
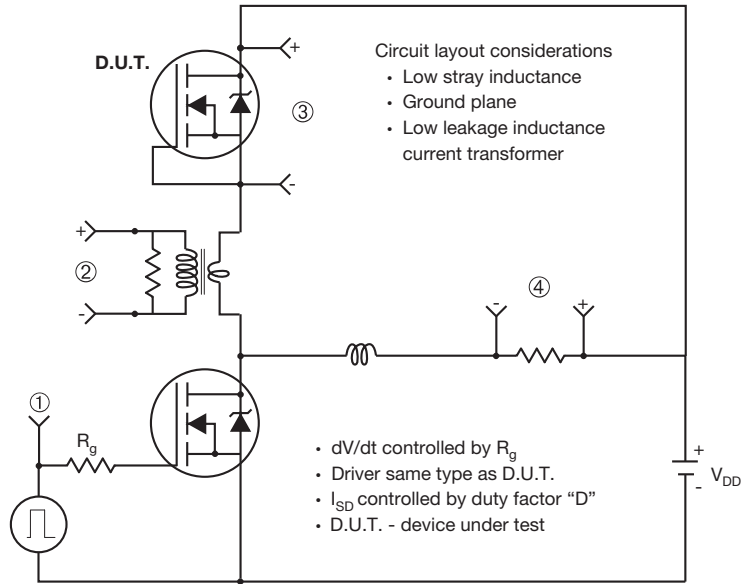


Fig. 17 - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit

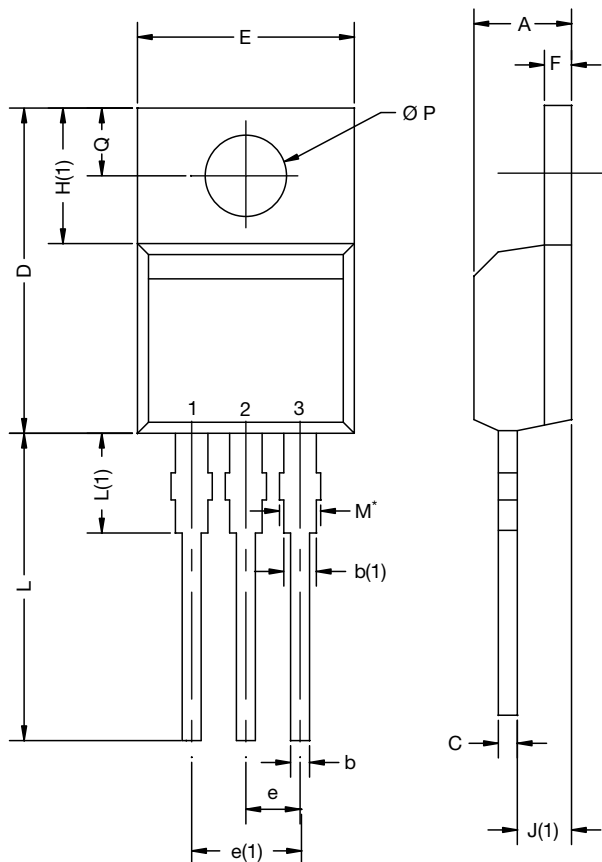


Note

a. $V_{GS} = 5\text{ V}$ for logic level devices

Fig. 14 - For N-Channel

TO-220-1

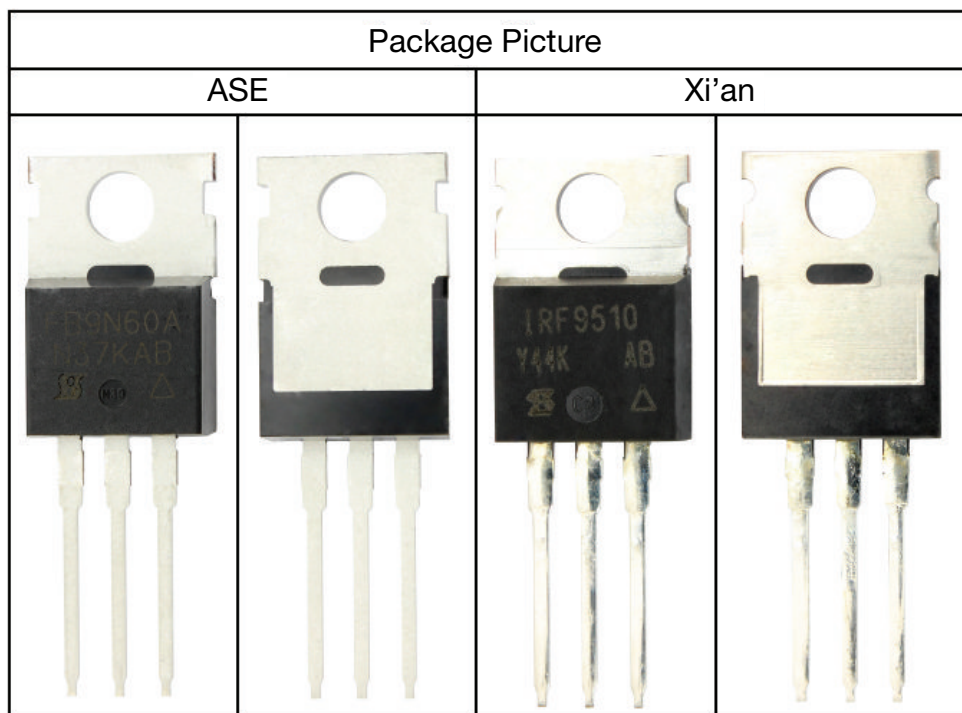


DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.24	4.65	0.167	0.183
b	0.69	1.02	0.027	0.040
b(1)	1.14	1.78	0.045	0.070
c	0.36	0.61	0.014	0.024
D	14.33	15.85	0.564	0.624
E	9.96	10.52	0.392	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.10	6.71	0.240	0.264
J(1)	2.41	2.92	0.095	0.115
L	13.36	14.40	0.526	0.567
L(1)	3.33	4.04	0.131	0.159
$\varnothing P$	3.53	3.94	0.139	0.155
Q	2.54	3.00	0.100	0.118

ECN: X15-0364-Rev. C, 14-Dec-15
DWG: 6031

Note

- M* = 0.052 inches to 0.064 inches (dimension including protrusion), heatsink hole for HVM





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